

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination GAO ET AL.	
		Examiner Thomas J. Magee	Art Unit 2811	Page 1 of 1

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	V	Syd R. Wilson, Clarence J. Tracy and John L. Freeman, Jr., "Handbook of Multilevel Metallization for Integrated Circuits," Noyes Publ., Westwood, N.J.(1993) p.42
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.